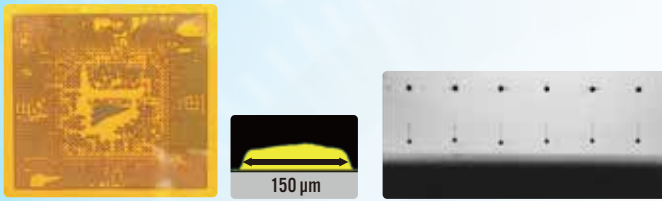


導電性銅ナノインク ラインナップ

Conductive Cu Nano Ink Line up

各印刷方法に対応 Compatible with each printing method

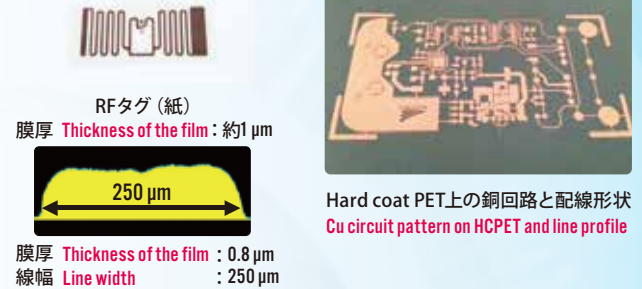
インクジェット印刷 Inkjet printing



PI上の銅回路と配線形状
Cu circuit pattern on PI and line profile

銅ナノインクの吐出液滴像
Jetting image of Cu nano ink droplet

フレキソ印刷 Flexographic printing

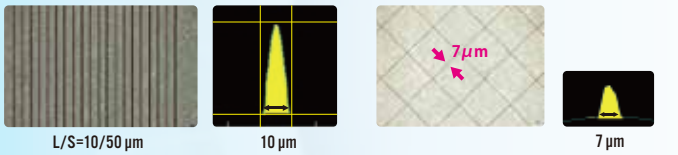


RFタグ(紙)
膜厚 Thickness of the film : 約1 μm

膜厚 Thickness of the film : 0.8 μm
線幅 Line width : 250 μm

Hard coat PET上の銅回路と配線形状
Cu circuit pattern on HCPET and line profile

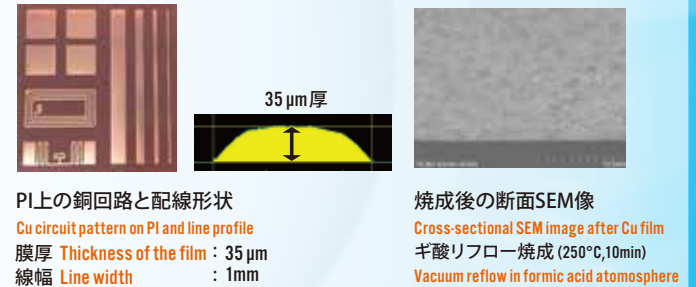
グラビアオフセット印刷 Gravure offset printing



Hard coat PET上の銅回路と配線形状
Cu circuit pattern on HCPET and line profile
膜厚 Thickness of the film : 1.6 μm
線幅 Line width : 12 μm

Hard coat PET上の銅メタルメッシュ
Cu metal mesh on HCPET
膜厚 Thickness of the film : 0.7 μm
線幅 Line width : 7 μm

スクリーン印刷 Screen printing



PI上の銅回路と配線形状
Cu circuit pattern on PI and line profile
膜厚 Thickness of the film : 35 μm
線幅 Line width : 1mm

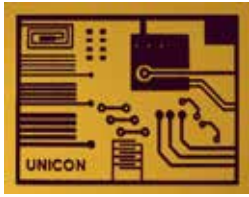
焼成後の断面SEM像
Cross-sectional SEM image after Cu film
真空リフロー焼成(250°C, 10min)
Vacuum reflow in formic acid atmosphere

銅ナノインク特性 Properties of Cu nano ink

型番 Ink No.	IJ-02	CC-02	F-03B	GO-01	GO-03	SC-03
印刷法 Printing Method	インクジェット Inkjet		フレキソ Flexographic	グラビアオフセット Gravure offset		スクリーン Screen
粒径 (nm)(M.D) Particle size (nm)(M.D)	40		80	>40		
粘度(mPa・s) Viscosity(mPa・s)	15±5	7.5±1	100-300	1000-6000		2.5±1.0 Pa・s
焼結(焼成)法 Sintering Method	キセノンフラッシュランプ Xenon Flash lamp					ギ酸リフロー Vacuum reflow in formic acid atmosphere
焼結温度 Sintering temperature	測定不可 Not measurable					150~250°C
焼結時間 Sintering time	0.5~10 msec.					10min.
適用基材 Applicable Substrate	PI, LCP, Glass		PI, Glass, Paper	PI, Glass		
体積抵抗率($\mu\Omega\cdot\text{cm}$) Resistivity($\mu\Omega\cdot\text{cm}$) after sintering	4~5		4~5(on PI and Glass) 7~9(on Paper)	9~10		3~5
密着性 (テープ剥離試験) Adhesion	良好(剥離なし) vs 上記基材 Good(No peeling) vs as above substrate					良好(剥離なし) vs プライマー塗布した上記基材 Good(No peeling) vs coated primer on above substrates
焼成後膜厚(μm) Film thickness after Sintering	0.5~1	0.2~0.5	1~3	<2	<1	10~30
L/S(μm)	100/100		50/50	線幅 Line width: 20~100 μm	線幅 Line width: 5~50 μm	70/70

銅ナノインク光焼成前後 (PI基材上) Cu nano ink by Photo-sintering on Polyimide before & after

PS前 (乾燥後) Before (after drying)

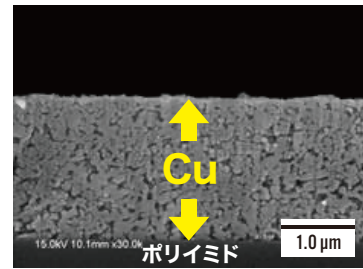


IJ印刷 (基材) : ポリイミド

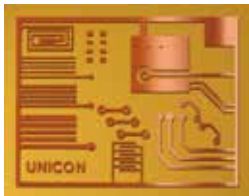
体積抵抗率: 測定不能

Resistivity ($\mu\Omega \cdot \text{cm}$)
before sintering: Not measurable

Before



PS後 After

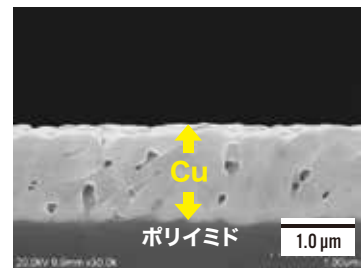


IJ印刷 (基材) : ポリイミド

体積抵抗率: 4~5 $\mu\Omega \cdot \text{cm}$

Resistivity ($\mu\Omega \cdot \text{cm}$)
after sintering: 4~5

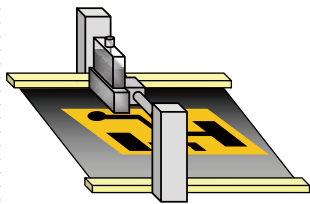
After



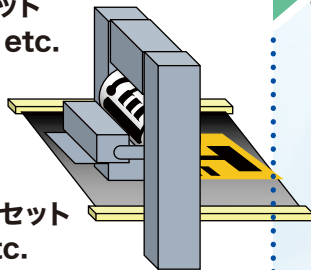
光焼成RtoRプロセス Process of Photo-sintering Roll to Roll

印刷 Printing

無版、有版
Plate, non-plate



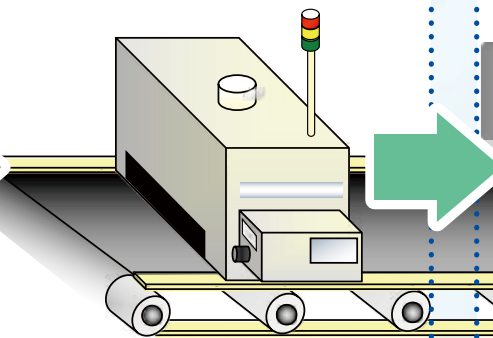
インクジェット
静電吐出 etc.
Inkjet



グラビアオフセット
フレキシ etc.
Gravure offset
Flexographic

乾燥 Drying

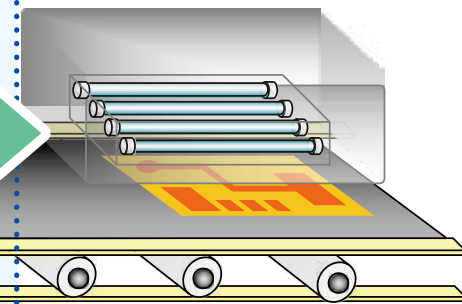
溶剤除去
環境: 大気下
温度: 室温~100°C以下
乾燥時間: 数秒~5分以内



Solvent removal
Environment: under the atmosphere
Temperature: room temperature~under 100°C
Drying time: a few seconds~within 5 minutes

光焼成 Photo-sintering

環境: 大気下、室温
温度: 瞬間的には高温
焼成時間: 1秒未満 (数ミリ秒)



Environment: atmosphere, room temperature
Temperature: momentarily high temperature
Time: less than 1 second

